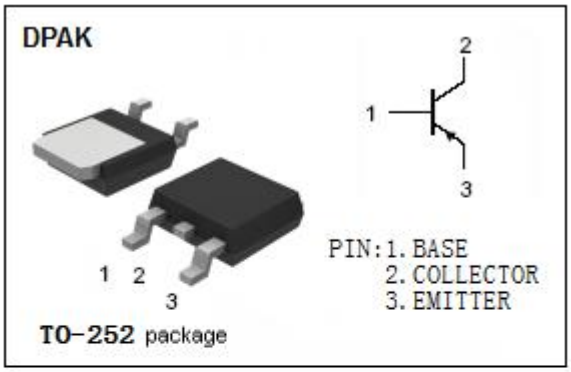
isc Silicon PNP Power Transistor — 2SB768

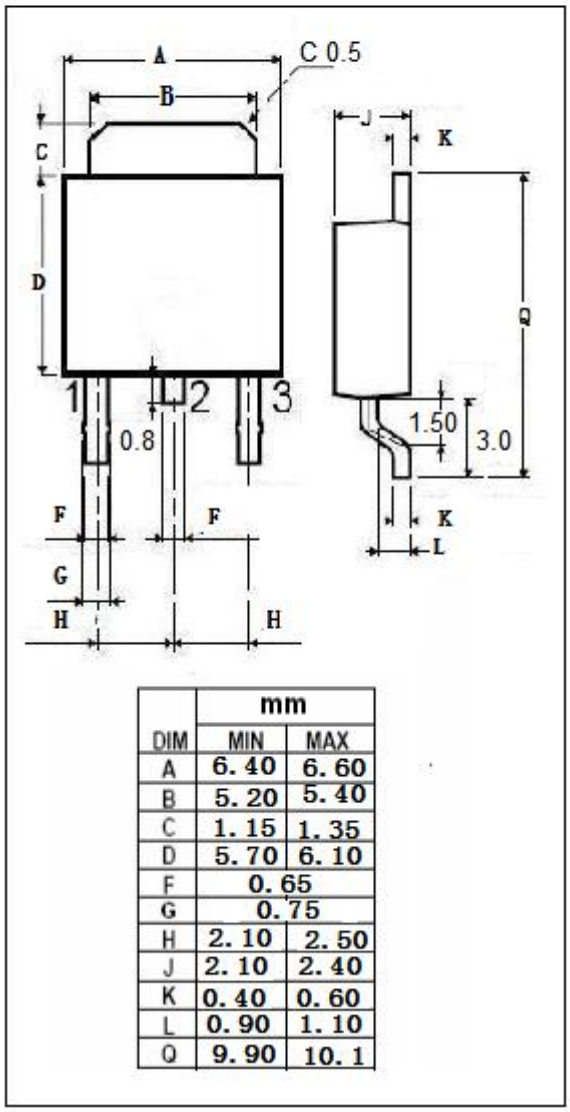


DESCRIPTION

- High voltage:V_{CEO}=-150V
- PNP silicon triple diffused transistor
- Complementary NPN types:2SD1033
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- The 2SB768 is designed for color TV vertical deflection output especially in hybrid integrated circuits



DIM	mm MIN	mm MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-3	A
P_C	Collector Power Dissipation @ Ta=25℃	2	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$NOTE	Collector-Emitter Saturation Voltage	I_C= -0.5A; I_B= -50mA			-1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -150V; I_E= 0			-50	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -4V; I_C= 0			-50	μA
h_{FE}NOTE	DC Current Gain	I_C= -0.4A; V_{CE}= -10V	40		200	
f_T	Current-Gain—Bandwidth Product	I_C= -0.4A; V_{CE}= -10V,f= 100MHz		10		MHz

NOTE:Pulse test PW≤350us,duty cycle ≤2%

◆ **h_{FE} Classifications**

M	L	K
40-80	60-120	100-200